



Shantou Huashan Electronic Devices Co., Ltd.

NPN SILICON TRANSISTOR

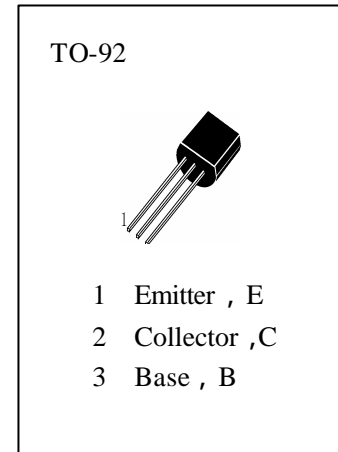
**H420**

**APPLICATIONS**

Class-B video output stages in colour television and professional monitor equipment

**ABSOLUTE MAXIMUM RATINGS (  $T_a=25$  )**

- $T_{stg}$ —Storage Temperature..... -55~150
- $T_j$ —Junction Temperature.....150
- $P_C$ —Collector Dissipation.....800mW
- $V_{CBO}$ —Collector-Base Voltage.....300V
- $V_{CEO}$ —Collector-Emitter Voltage.....300V
- $V_{EBO}$ —Emitter-Base Voltage.....5V
- $I_C$ —Collector Current.....50mA



**ELECTRICAL CHARACTERISTICS (  $T_a=25$  )**

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	300			V	$I_C=100 \mu A, I_E=0$
BVCER	Collector-Emitter Breakdown Voltage	300			V	$I_C=1 mA, R_{BE}=2.7K$
HFE	DC Current Gain	50				$V_{CE}=20V, I_C=25 mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			0.6	V	$I_C=30mA, I_B=5 mA$
ICBO	Collector Cut-off Current			10	nA	$V_{CB}=200V, I_E=0$
IEBO	Emitter Cut-off Current			10	$\mu A$	$V_{EB}=5V, I_C=0$
Crb	feedback Capacitance			1.6	pF	$V_{CE}=30V, I_C=0, f=1MHz$
fr	Current Gain-Bandwidth Product	60			MHz	$V_{CE}=10V, I_C=10mA$